

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
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**TYPE:6PT2202N1T \* \***

CHIP SIZE	0.4 * 0.4mm
WAFER SIZE	6inch
POSSIBLE DIE PER WAFER	95,200pcs

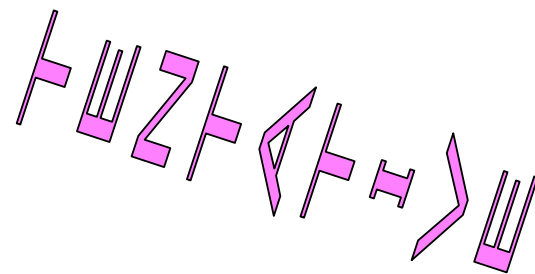
Maximum Ratings(Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	20	V
Gate-source voltage	VGSS	±8	V

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS1			±2	uA	VGS=±8V VDS=0V
2	IGSS2			±0.5	uA	VGS=±4.5V VDS=0V
3	IDSS			0.5	uA	VDS=20V VGS=0V
4	BVDSS	22			V	ID=100uA
5	VTH	0.53		0.95	V	ID=250uA
6	RDS(on)1		0.4	0.6	Ω	VGS=4.5V, ID=540mA
7	RDS(on)2		0.5	0.75	Ω	VGS=2.5V, ID=500mA
8	RDS(on)3		0.7	1.2		VGS=1.8V, ID=350mA
9	VSD	0.5		1.1	V	I=115mA VGS=0V
10	Yfs	400			mS	VDS=10V Id=200mA

※ Built-in ZD between Gate and Source.



NOTE: